

General Purpose Transistors

PNP Silicon

● FEATURES

- 1) We declare that the material of product compliant with RoHS requirements and Halogen Free.
- 2) S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

● DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LMBT2907ALT1G	2F	3000/Tape&Reel
LMBT2907ALT3G	2F	10000/Tape&Reel

● MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-Emitter Voltage	V_{CEO}	-60	Vdc
Collector-Base Voltage	V_{CBO}	-60	Vdc
Emitter-Base Voltage	V_{EBO}	-5	Vdc
Collector Current — Continuous	I_C	-600	mAdc

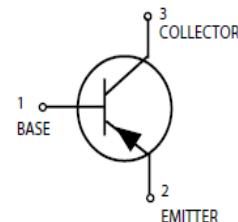
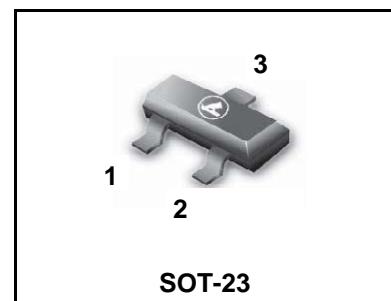
● THERMAL CHARACTERISTICS

Total Device Dissipation, FR-5 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation, Alumina Substrate (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

LMBT2907ALT1G
S-LMBT2907ALT1G



LMBT2907ALT1G,S-LMBT2907ALT1G

●ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector-Emitter Breakdown Voltage ($I_c = -10 \text{ mA}_\text{dc}$, $I_B = 0$)	$V_{BR}(\text{CEO})$	-60	-	-	V
Collector-Base Breakdown Voltage ($I_c = -10 \mu\text{A}_\text{dc}$, $I_E = 0$)	$V_{BR}(\text{CBO})$	-60	-	-	V
Emitter-Base Breakdown Voltage ($I_E = -10 \mu\text{A}_\text{dc}$, $I_c = 0$)	$V_{BR}(\text{EBO})$	-5	-	-	V
Collector Cutoff Current ($V_{CB} = -30 \text{ V}_\text{dc}$, $V_{EB(\text{off})} = -5.0 \text{ V}_\text{dc}$)	I_{CEX}	-	-	-50	nA
Collector Cutoff Current ($V_{CB} = -50 \text{ V}_\text{dc}$, $I_E = 0$) ($V_{CB} = -50 \text{ V}_\text{dc}$, $I_E = 0$, $T_a = 125^\circ C$)	I_{CBO}	-	-	-0.01	μA
Base Current ($V_{CE} = -30 \text{ V}_\text{dc}$, $V_{EB(\text{off})} = -0.5 \text{ V}_\text{dc}$)	I_B	-	-	-50	nA

ON CHARACTERISTICS (Note 1.)

DC Current Gain ($I_c = -0.1 \text{ mA}_\text{dc}$, $V_{CE} = -10 \text{ V}_\text{dc}$) ($I_c = -1.0 \text{ mA}_\text{dc}$, $V_{CE} = -10 \text{ V}_\text{dc}$) ($I_c = -10 \text{ mA}_\text{dc}$, $V_{CE} = -10 \text{ V}_\text{dc}$) ($I_c = -150 \text{ mA}_\text{dc}$, $V_{CE} = -10 \text{ V}_\text{dc}$) (3) ($I_c = -500 \text{ mA}_\text{dc}$, $V_{CE} = -10 \text{ V}_\text{dc}$) (3)	h_{FE}	75 100 100 100 50	- - - - -	- - - 300 -	
Collector-Emitter Saturation Voltage (3) ($I_c = -150 \text{ mA}_\text{dc}$, $I_B = -15 \text{ mA}_\text{dc}$) ($I_c = -500 \text{ mA}_\text{dc}$, $I_B = -50 \text{ mA}_\text{dc}$)	$V_{CE(\text{sat})}$	- -	- -	-0.4 -1.6	V
Base-Emitter Saturation Voltage ($I_c = -150 \text{ mA}_\text{dc}$, $I_B = -15 \text{ mA}_\text{dc}$) ($I_c = -500 \text{ mA}_\text{dc}$, $I_B = -50 \text{ mA}_\text{dc}$)	$V_{BE(\text{sat})}$	- -	- -	-1.3 -2.6	V

SMALL-SIGNAL CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Current-Gain — Bandwidth Product (4) ($I_c = -50 \text{ mA}_\text{dc}$, $V_{CE} = -20 \text{ V}_\text{dc}$, $f = 100 \text{ MHz}$)	f_T	200	-	-	MHz
Output Capacitance ($V_{CB} = -10 \text{ V}_\text{dc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{obo}	-	-	8	pF
Input Capacitance ($V_{EB} = -2.0 \text{ V}_\text{dc}$, $I_c = 0$, $f = 1.0 \text{ MHz}$)	C_{ibo}	-	-	30	pF

SWITCHING CHARACTERISTICS

Turn-On Time	$(V_{CC} = -30 \text{ V}_\text{dc}$, $I_c = -150 \text{ mA}_\text{dc}$, $I_{B1} = -15 \text{ mA}_\text{dc}$)	t_{on}	-	-	45	ns
Delay Time		t_d	-	-	10	
Rise Time		t_r	-	-	40	
Storage Time	$(V_{CC} = -6 \text{ V}_\text{dc}$, $I_c = -150 \text{ mA}_\text{dc}$, $I_{B1} = I_{B2} = -15 \text{ mA}_\text{dc}$)	t_s	-	-	225	
Fall Time		t_f	-	-	60	
Turn-Off Time		t_{off}	-	-	280	

3. Pulse Test: Pulse Width <300 μs , Duty Cycle <2.0%.

4. f_T is defined as the frequency at which h_{FE} extrapolates to unity.

LMBT2907ALT1G,S-LMBT2907ALT1G

ELECTRICAL CHARACTERISTICS CURVES

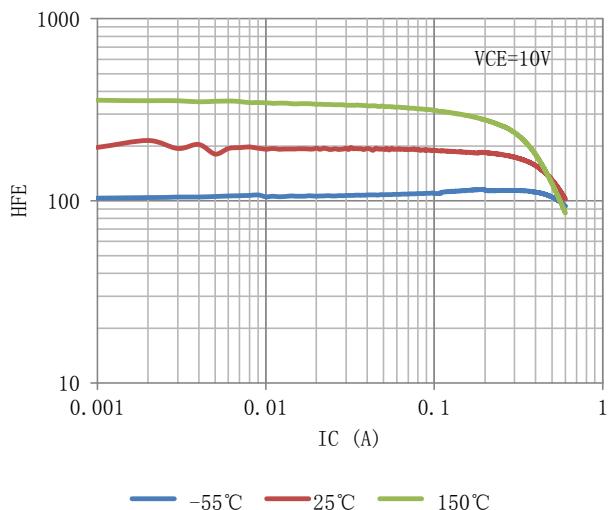


Figure 1. DC Current Gain

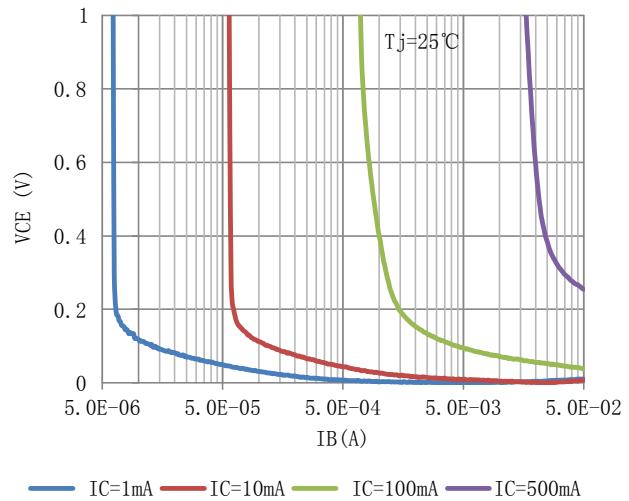


Figure 2. Collector Saturation Region

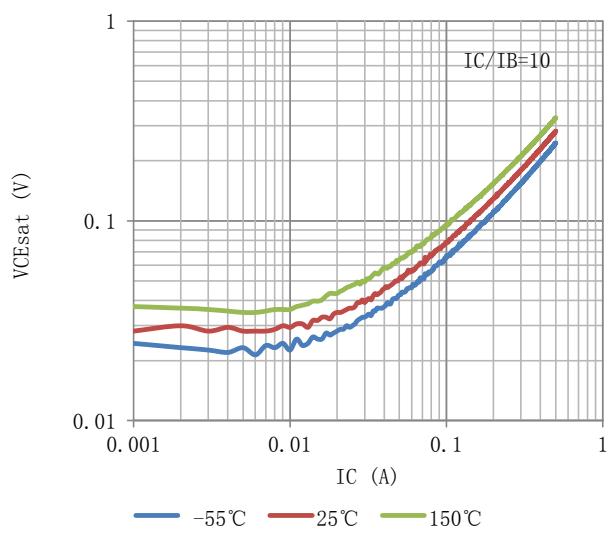


Figure 3. Collector Emitter Saturation Voltage vs.
Collector Current

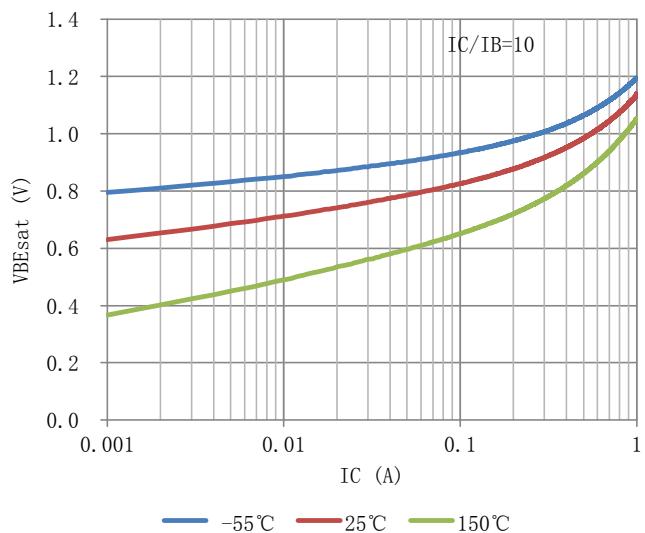


Figure 4. Base Emitter Saturation Voltage vs.
Collector Current

LMBT2907ALT1G,S-LMBT2907ALT1G

ELRCTRICAL CHARACTERISTICS CURVES

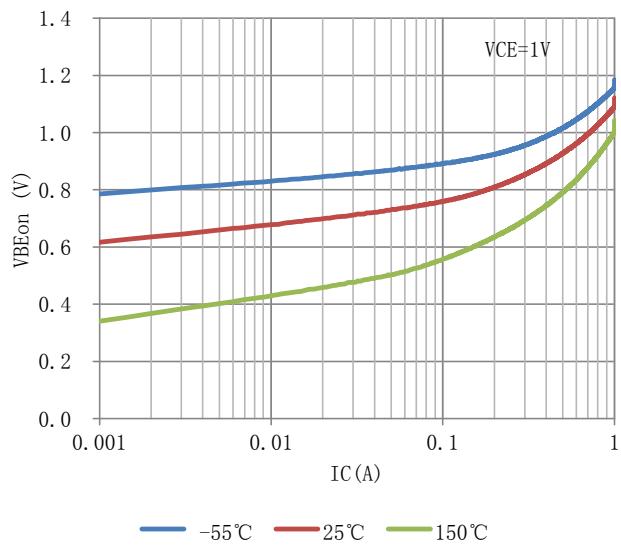


Figure 5. Base Emitter Voltage vs. Collector Current

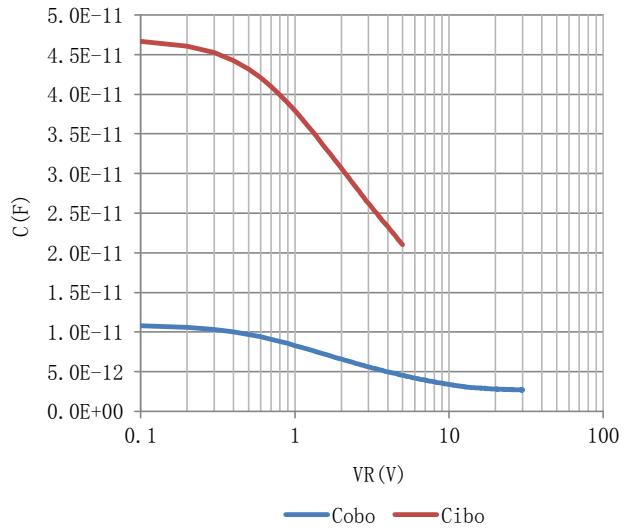


Figure 6. Capacitance

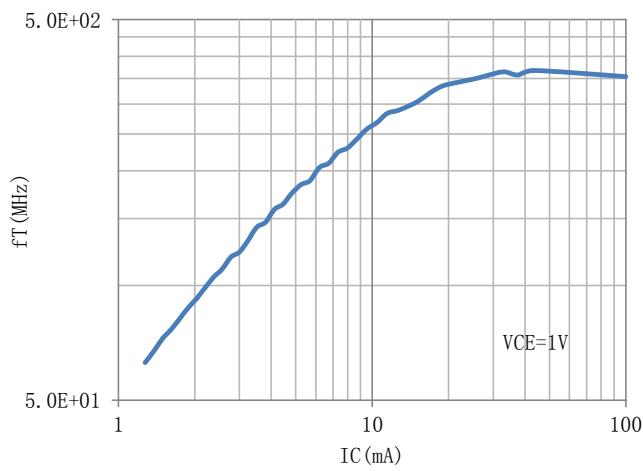
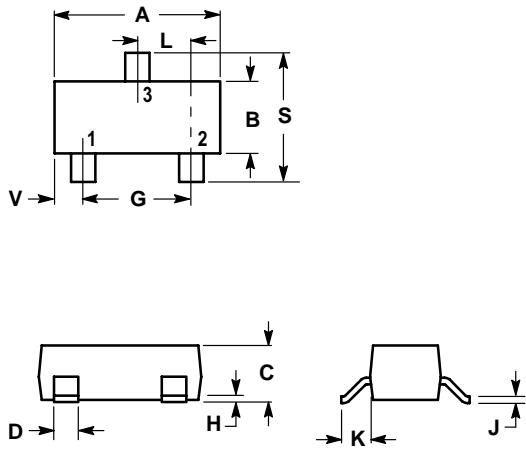


Figure 7. Current-Gain Bandwidth Product

LMBT2907ALT1G,S-LMBT2907ALT1G

SOT-23



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

